Choelhwyi Bae

List of Publications by Year
in descending order

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16	275	1162367	940134
papers	citations	8	16
		h-index	g-index

16	16	16	320
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Characteristics of HfO2 thin films grown by plasma atomic layer deposition. Applied Physics Letters, 2005, 87, 053108.	1.5	54
2	Surface passivation of n-GaN by nitrided-thin-Ga2O3â^•SiO2 and Si3N4 films. Journal of Applied Physics, 2004, 96, 2674-2680.	1.1	41
3	Composition, structure, and electrical characteristics of HfO2 gate dielectrics grown using the remote- and direct-plasma atomic layer deposition methods. Journal of Applied Physics, 2005, 98, 094504.	1.1	40
4	Electron trapping in metal-insulator-semiconductor structures on n-GaN with SiO2 and Si3N4 dielectrics. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 2379-2383.	0.9	28
5	Low-temperature preparation of GaN-SiO2 interfaces with low defect density. I. Two-step remote plasma-assisted oxidation-deposition process. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 2402-2410.	0.9	26
6	Suppression of parasitic Si substrate oxidation in HfO2â€“ultrathin-Al2O3â€“Si structures prepared by atomic layer deposition. Applied Physics Letters, 2005, 86, 252110.	1.5	22
7	Effects of N2 remote plasma nitridation on the structural and electrical characteristics of the HfO2 gate dielectrics grown using remote plasma atomic layer deposition methods. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2006, 24, 900-907.	0.9	14
8	Work-function difference between Al and n-GaN from Al-gated n-GaNâ^•nitrided-thin-Ga2O3â^•SiO2 metal oxide semiconductor structures. Applied Physics Letters, 2004, 84, 5413-5415.	1.5	13
9	Effect of Buffer Layer for HfO[sub 2] Gate Dielectrics Grown by Remote Plasma Atomic Layer Deposition. Journal of the Electrochemical Society, 2007, 154, H97.	1.3	8
10	Low temperature semiconductor surface passivation for nanoelectronic device applications. Surface Science, 2003, 532-535, 759-763.	0.8	7
11	Effects of Remote Plasma Pre-oxidation of Si Substrates on the Characteristics of ALD-Deposited HfO[sub 2] Gate Dielectrics. Electrochemical and Solid-State Letters, 2006, 9, G211.	2.2	6
12	Low-temperature preparation of GaN-SiO2 interfaces with low defect density. II. Remote plasma-assisted oxidation of GaN and nitrogen incorporation. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 2411-2418.	0.9	5
13	Remote Plasma Atomic Layer Deposition of HfO[sub 2] Thin Films Using the Alkoxide Precursor Hf(mp)[sub 4]. Electrochemical and Solid-State Letters, 2006, 9, G200.	2.2	4
14	Effects of N[sub 2] RPN on the Structural and Electrical Characteristics of Remote Plasma Atomic Layer-Deposited HfO[sub 2] Films. Electrochemical and Solid-State Letters, 2006, 9, F13.	2.2	3
15	Characteristics of Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors with HfO2/SiO2/Si and HfO2/SiOxNy/Si Stack Structures Formed by Remote Plasma Technique. Japanese Journal of Applied Physics, 2008, 47, 6196-6199.	0.8	3
16	Characteristics of remote plasma atomic layer-deposited HfO2 films on O2 and N2 plasma-pretreated Si substrates. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2006, 24, 678-681.	0.9	1